

Phase Control Thyristors (Hockey PUK Version), 720 A



E-PUK (TO-200AB)

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case E-PUK (TO-200AB)
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

PRIMARY CHARACTERISTICS

$I_{T(AV)}$	720 A
V_{DRM}/V_{RRM}	400 V, 800 V, 1200 V, 1400 V, 1600 V
V_{TM}	1.96 V
I_{GT}	100 mA
T_J	-40 °C to +125 °C
Package	E-PUK (TO-200AB)
Circuit configuration	Single SCR

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		720	A
	T_{hs}	55	°C
$I_{T(RMS)}$		1420	A
	T_{hs}	25	°C
I_{TSM}	50 Hz	9000	A
	60 Hz	9420	
I^2t	50 Hz	405	kA ² s
	60 Hz	370	
V_{DRM}/V_{RRM}		400 to 1600	V
t_q	Typical	100	μs
T_J		-40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-ST330C..C	04	400	500	50
	08	800	900	
	12	1200	1300	
	14	1400	1500	
	16	1600	1700	



ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average on-state current at heatsink temperature	$I_{T(AV)}$	180° conduction, half sine wave double side (single side) cooled	720 (350)	A
			55 (75)	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 25 °C heatsink temperature double side cooled	1420	
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	9000
		t = 8.3 ms	No voltage reapplied	9420
		t = 10 ms	100 % V_{RRM} reapplied	7570
		t = 8.3 ms	100 % V_{RRM} reapplied	7920
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied	405
		t = 8.3 ms	No voltage reapplied	370
		t = 10 ms	100 % V_{RRM} reapplied	287
		t = 8.3 ms	100 % V_{RRM} reapplied	262
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied	4050	$kA^2\sqrt{s}$
Low level value of threshold voltage	$V_{T(TO)1}$	$(16.7 \% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ maximum	0.91	V
High level value of threshold voltage	$V_{T(TO)2}$	$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum	0.92	
Low level value of on-state slope resistance	r_{t1}	$(16.7 \% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ maximum	0.58	$m\Omega$
High level value of on-state slope resistance	r_{t2}	$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum	0.57	
Maximum on-state voltage	V_{TM}	$I_{pk} = 1810$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine pulse	1.96	V
Maximum holding current	I_H	$T_J = 25$ °C, anode supply 12 V resistive load	600	mA
Typical latching current	I_L		1000	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	di/dt	Gate drive 20 V, 20 Ω , $t_r \leq 1$ μs $T_J = T_J$ maximum, anode voltage ≤ 80 % V_{DRM}	1000	A/ μs
Typical delay time	t_d	Gate current 1 A, $di_g/dt = 1$ A/ μs $V_d = 0.67$ % V_{DRM} , $T_J = 25$ °C	1.0	μs
Typical turn-off time	t_q	$I_{TM} = 550$ A, $T_J = T_J$ maximum, $di/dt = 40$ A/ μs , $V_R = 50$ V, $dV/dt = 20$ V/ μs , gate 0 V 100 Ω , $t_p = 500$ μs	100	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/ μs
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	50	mA



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			TYP.	MAX.	
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms	10.0		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$	2.0		
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms	3.0		A
Maximum peak positive gate voltage	$+V_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms	20		V
Maximum peak negative gate voltage	$-V_{GM}$		5.0		
DC gate current required to trigger	I_{GT}	$T_J = -40$ °C	200	-	mA
		$T_J = 25$ °C	100	200	
		$T_J = 125$ °C	50	-	
DC gate voltage required to trigger	V_{GT}	$T_J = -40$ °C	2.5	-	V
		$T_J = 25$ °C	1.8	3.0	
		$T_J = 125$ °C	1.1	-	
DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum	10		mA
DC gate voltage not to trigger	V_{GD}		0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	T_J		-40 to 125	°C	
Maximum storage temperature range	T_{Stg}		-40 to 150		
Maximum thermal resistance, junction to heatsink	R_{thJ-hs}	DC operation single side cooled	0.09	K/W	
		DC operation double side cooled	0.04		
Maximum thermal resistance, case to heatsink	R_{thC-hs}	DC operation single side cooled	0.02		
		DC operation double side cooled	0.01		
Mounting force, ± 10 %			9800 (1000)	N (kg)	
Approximate weight			83	g	
Case style		See dimensions - link at the end of datasheet	E-PUK (TO-200AB)		

ΔR_{thJ-hs} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.012	0.011	0.008	0.007	T _J = T _J maximum	K/W
120°	0.014	0.012	0.014	0.013		
90°	0.017	0.015	0.019	0.017		
60°	0.025	0.022	0.026	0.023		
30°	0.043	0.036	0.043	0.037		

Note

- The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

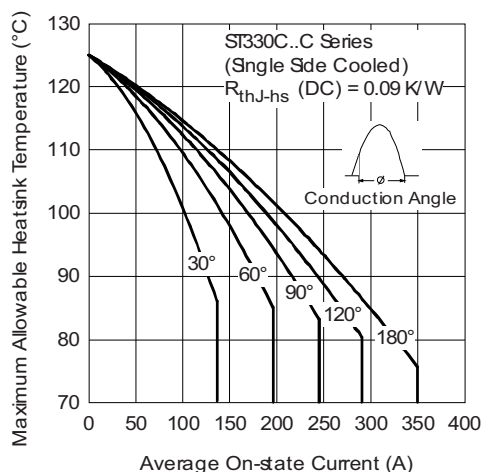


Fig. 1 - Current Ratings Characteristics

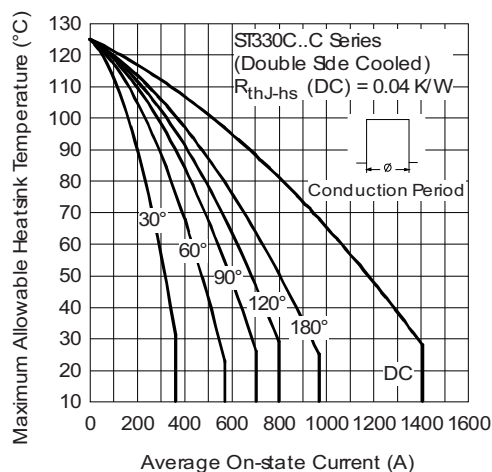


Fig. 4 - Current Ratings Characteristics

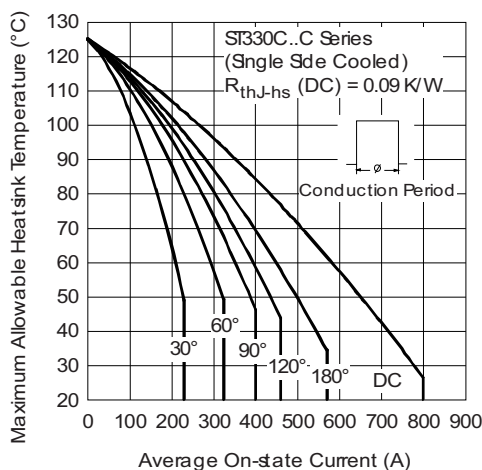


Fig. 2 - Current Ratings Characteristics

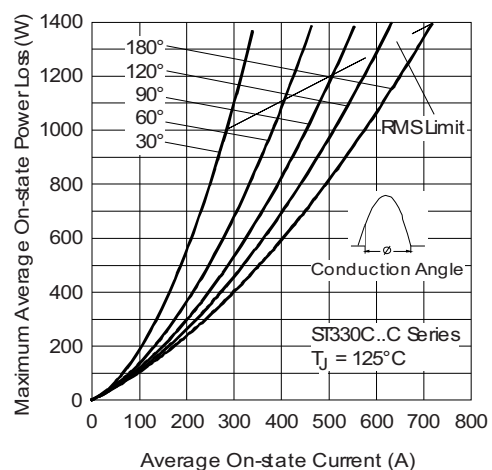


Fig. 5 - On-State Power Loss Characteristics

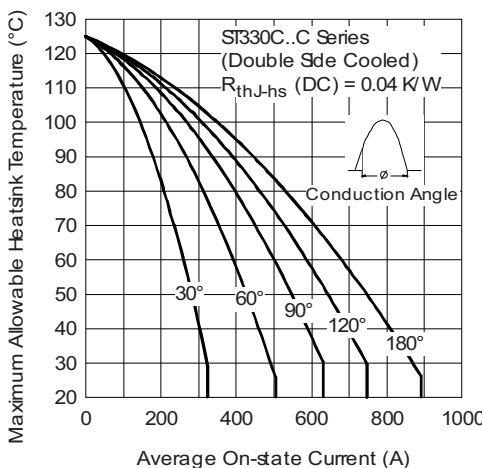


Fig. 3 - Current Ratings Characteristics

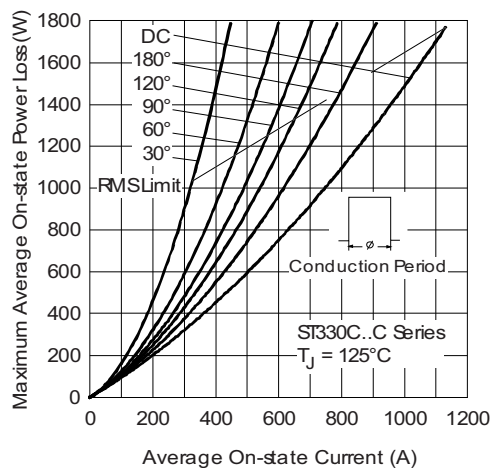


Fig. 6 - On-State Power Loss Characteristics

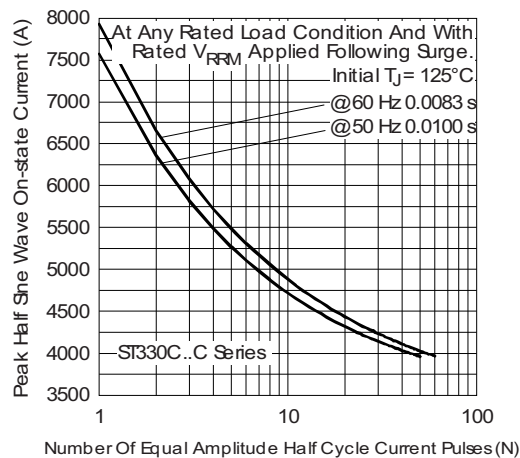


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

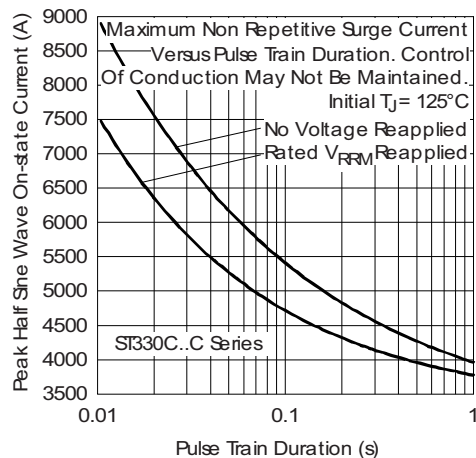


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

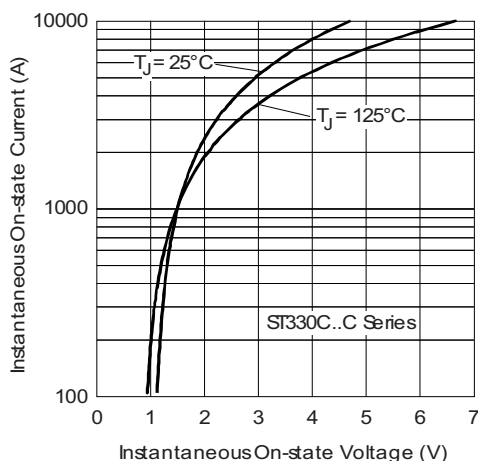


Fig. 9 - On-State Voltage Drop Characteristics

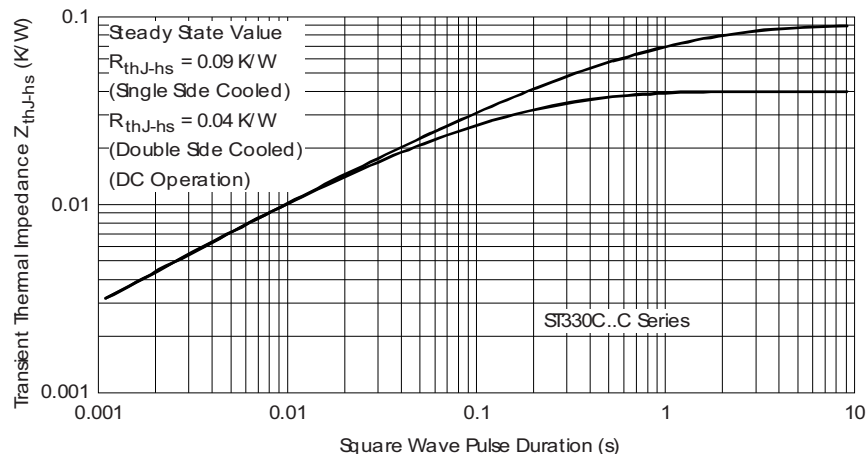


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

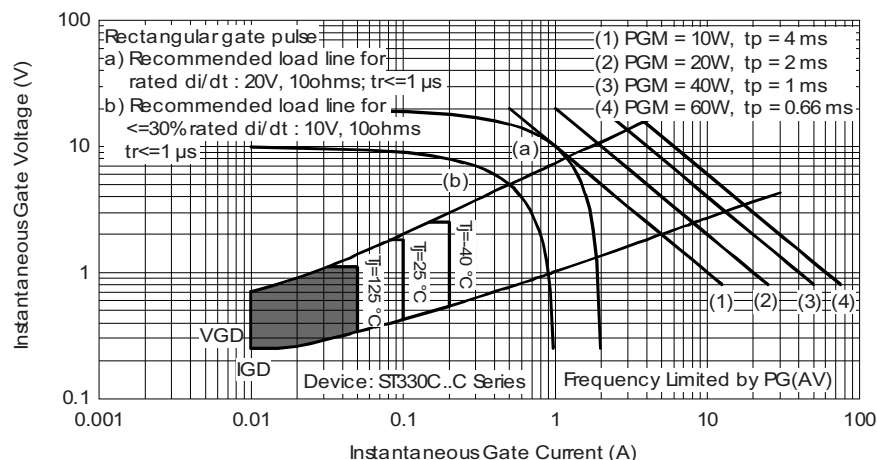


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	ST	33	0	C	16	C	1	-
	(1)	(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)

1	-	Vishay Semiconductors product
2	-	Thyristor
3	-	Essential part number
4	-	0 = converter grade
5	-	C = ceramic PUK
6	-	Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
7	-	C = PUK case E-PUK (TO-200AB)
8	-	0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)
		1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)
		2 = eyelet terminals (gate and auxiliary cathode soldered leads)
		3 = fast-on terminals (gate and auxiliary cathode soldered leads)
9	-	Critical dV/dt : • None = 500 V/ μs (standard selection)
		• L = 1000 V/ μs (special selection)

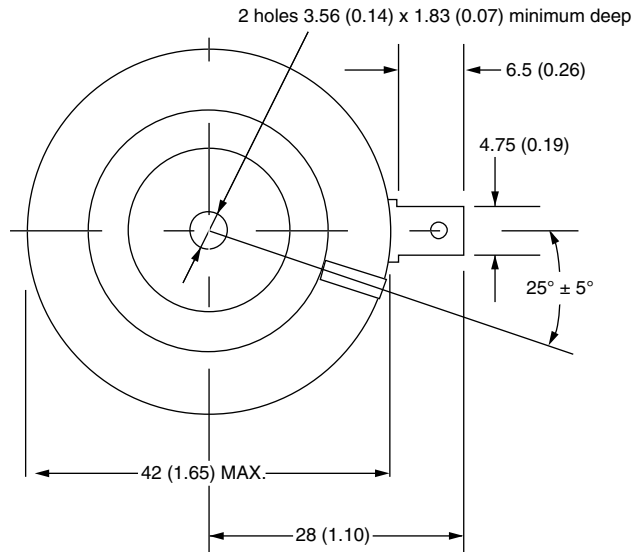
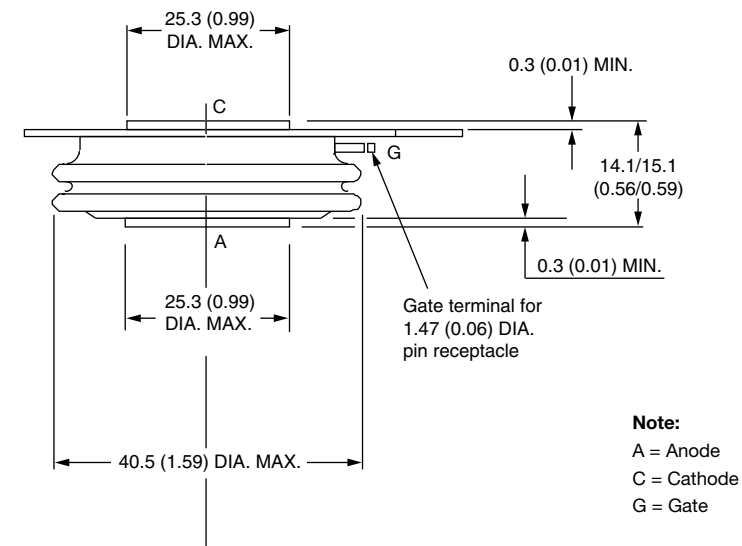
LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95075



E-PUK (TO-200AB)

DIMENSIONS in millimeters (inches)

Anode to gate
Creepage distance: 11.18 (0.44) minimum
Strike distance: 7.62 (0.30) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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